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Iwafuchi et al.

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(45) **Date of Patent:** ** **Jan. 13, 2004**

(54) **SEMICONDUCTOR ELEMENT**

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(73) Assignee: **Sony Corporation**, Tokyo (JP)

(**) Term: **14 Years**

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(51) **LOC (7) Cl.** **13-03**
(52) **U.S. Cl.** **D13/182**
(58) **Field of Search** D13/182; D14/172, D14/212, 233; 257/10, 77, 103, 190, 622, 627; 216/11; 313/309, 310, 311, 327; 428/332; 438/20; 445/24, 50, 51, 58

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(57) **CLAIM**

The ornamental design for a semiconductor element, as shown and described.

DESCRIPTION

FIG. **1** is a top, left, front perspective view of a semiconductor element showing our new design;

FIG. **2** is a bottom, left, front perspective view thereof;

FIG. **3** is a front elevational view thereof; and

FIG. **4** is a rear elevational view thereof.

FIG. **5** is a left side elevational view thereof;

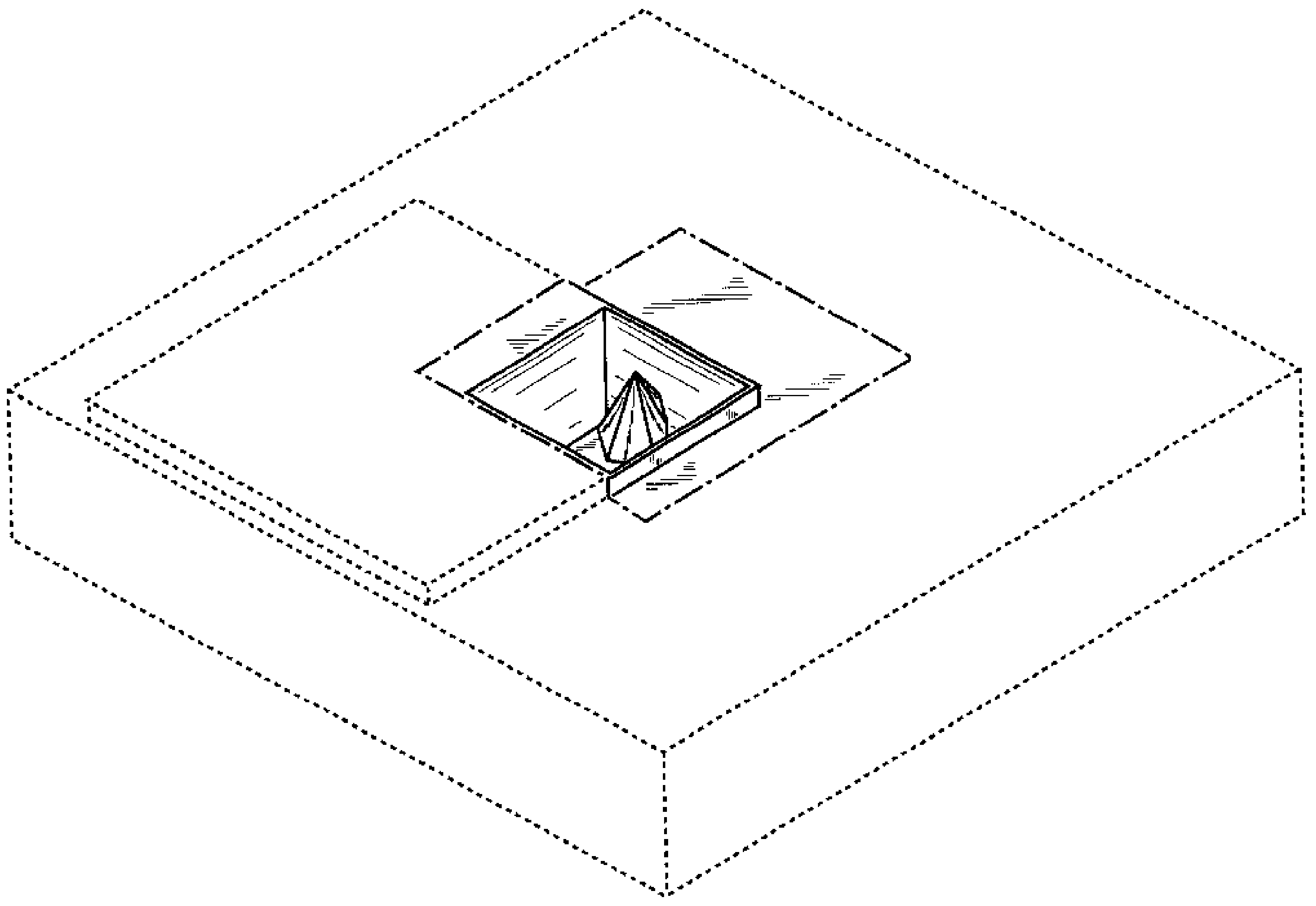
FIG. **6** is a right side elevational view thereof;

FIG. **7** is a top plan view thereof; and,

FIG. **8** is a bottom plan view thereof.

The portions in even broken lines are for illustrative purposes only and form no part of the claimed design. The portions in dot-dash broken lines define, but are not included in, the boundaries of the claimed design.

1 Claim, 5 Drawing Sheets



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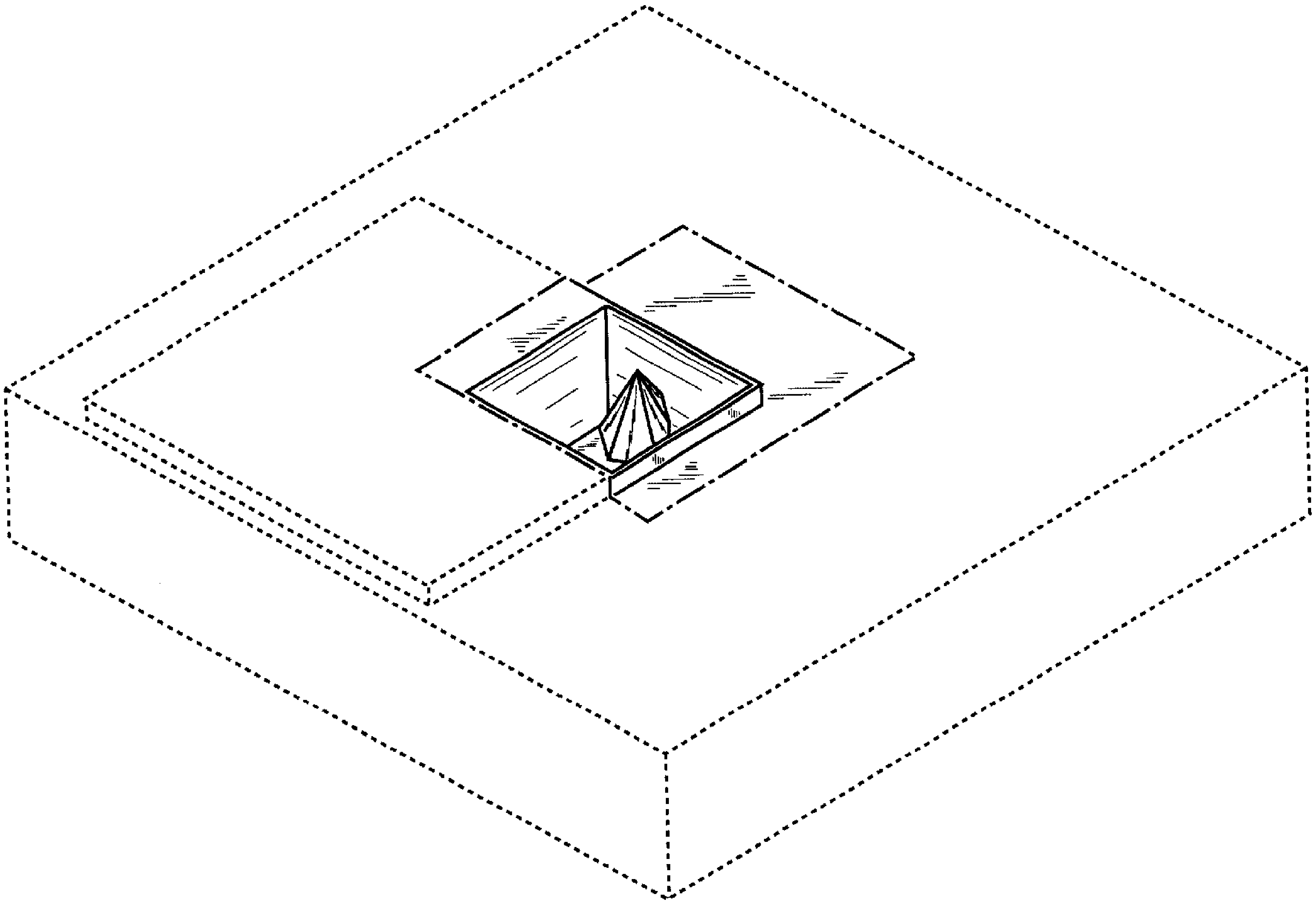


Fig. 1

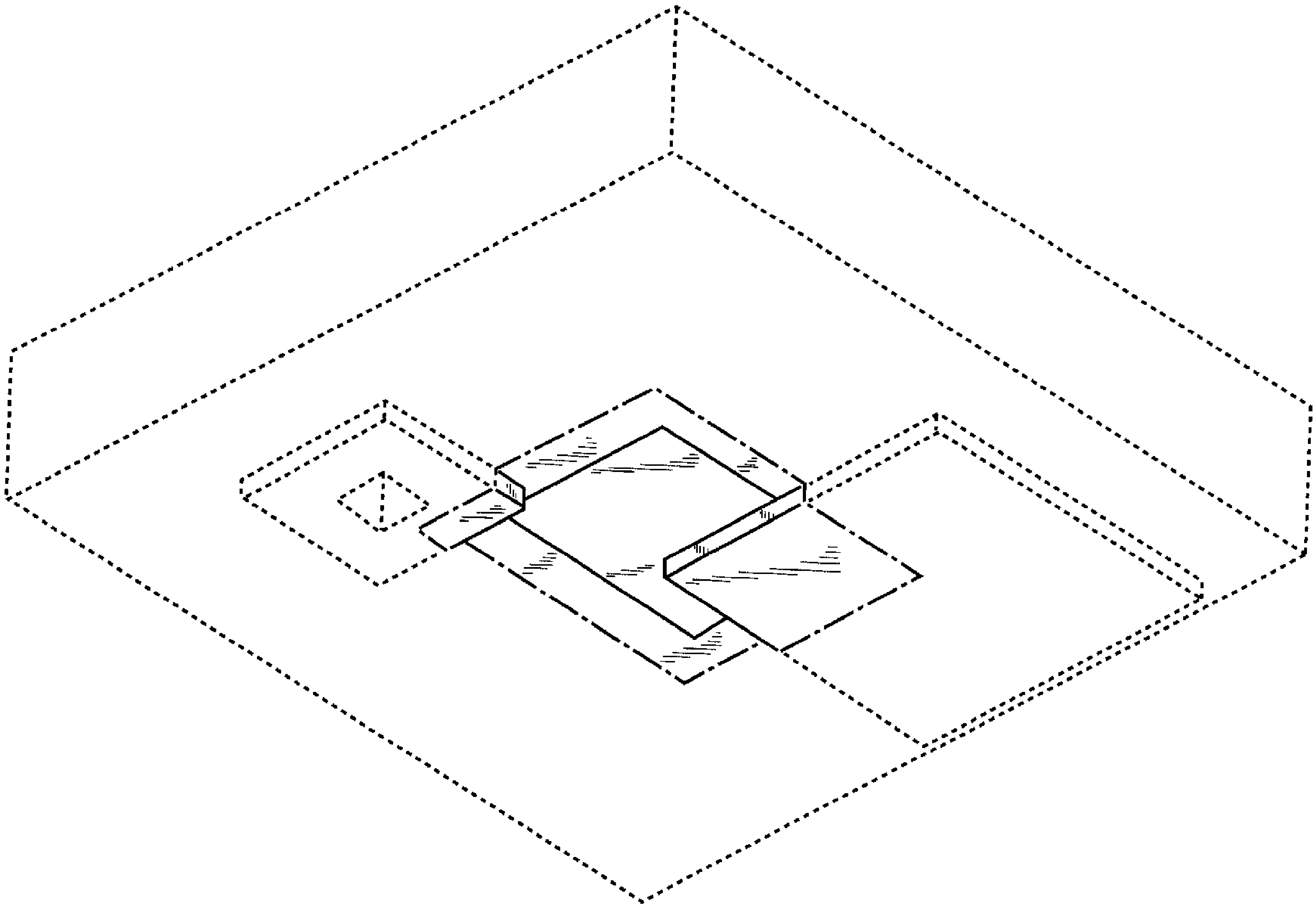


Fig. 2

Fig. 3

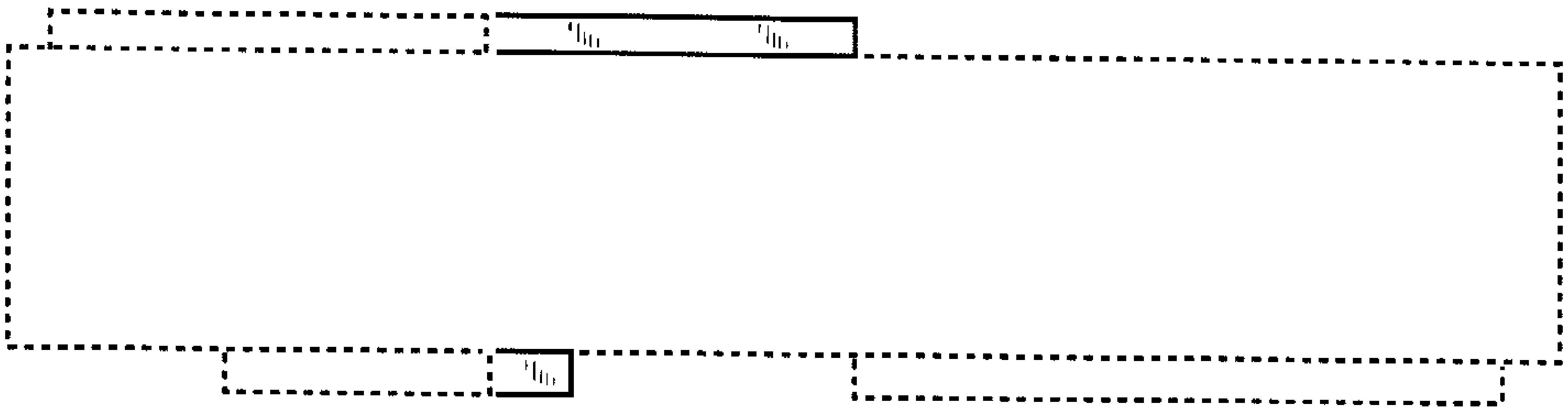


Fig. 4

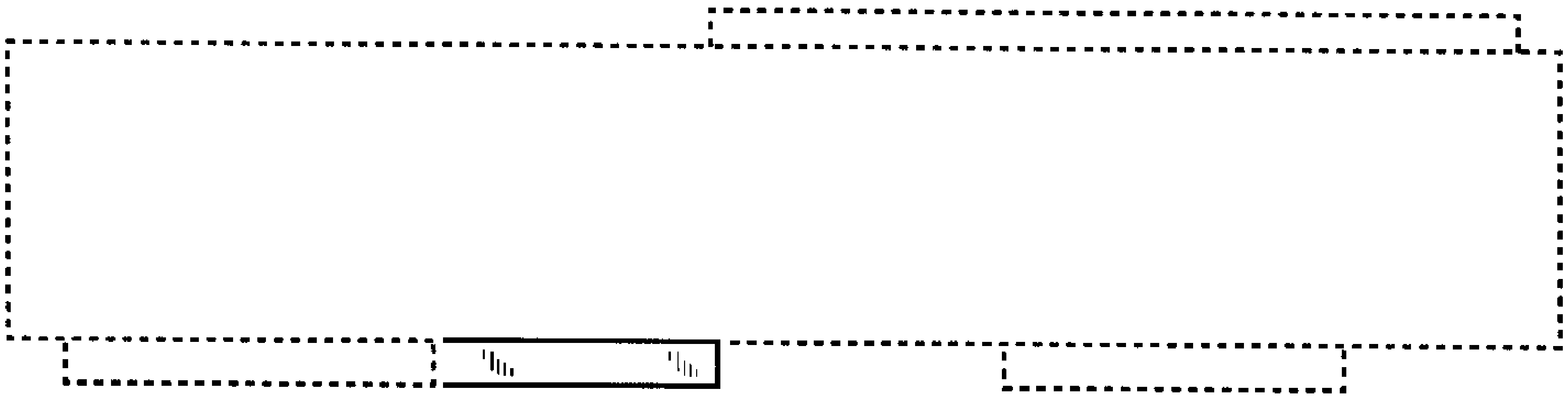


Fig. 5

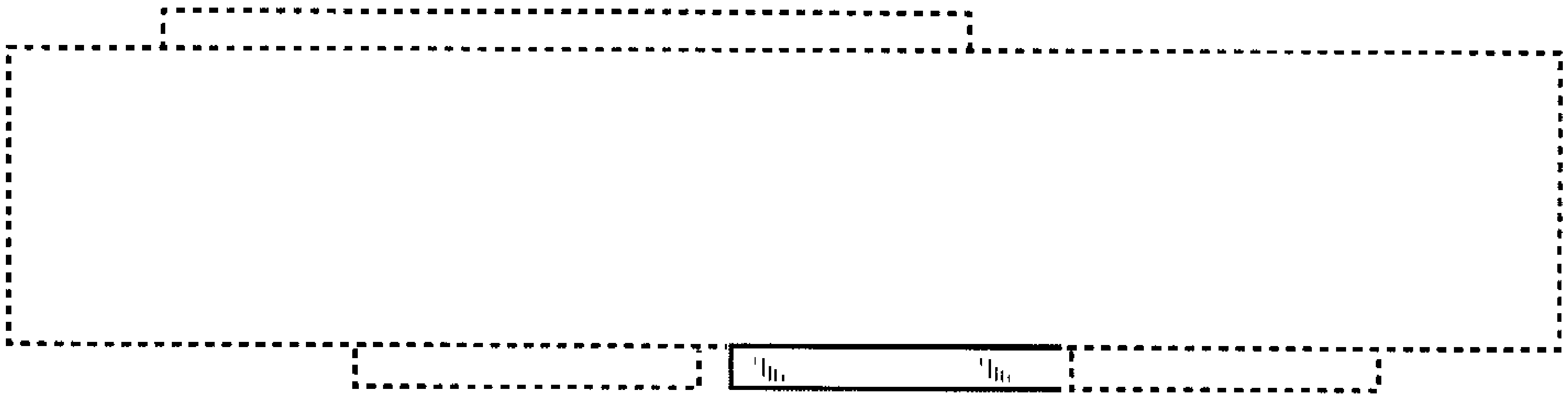
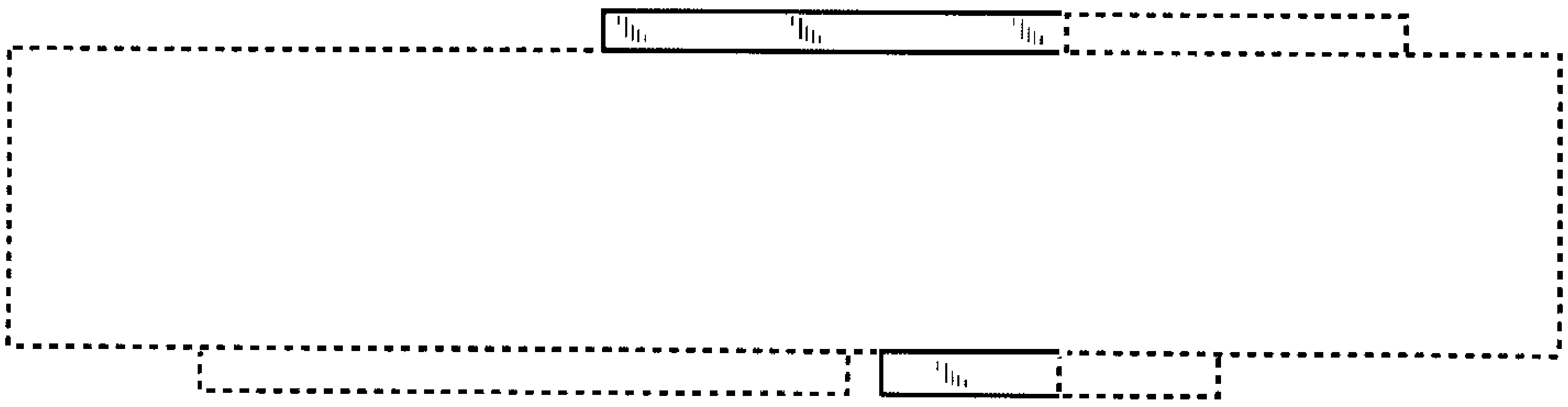


Fig. 6



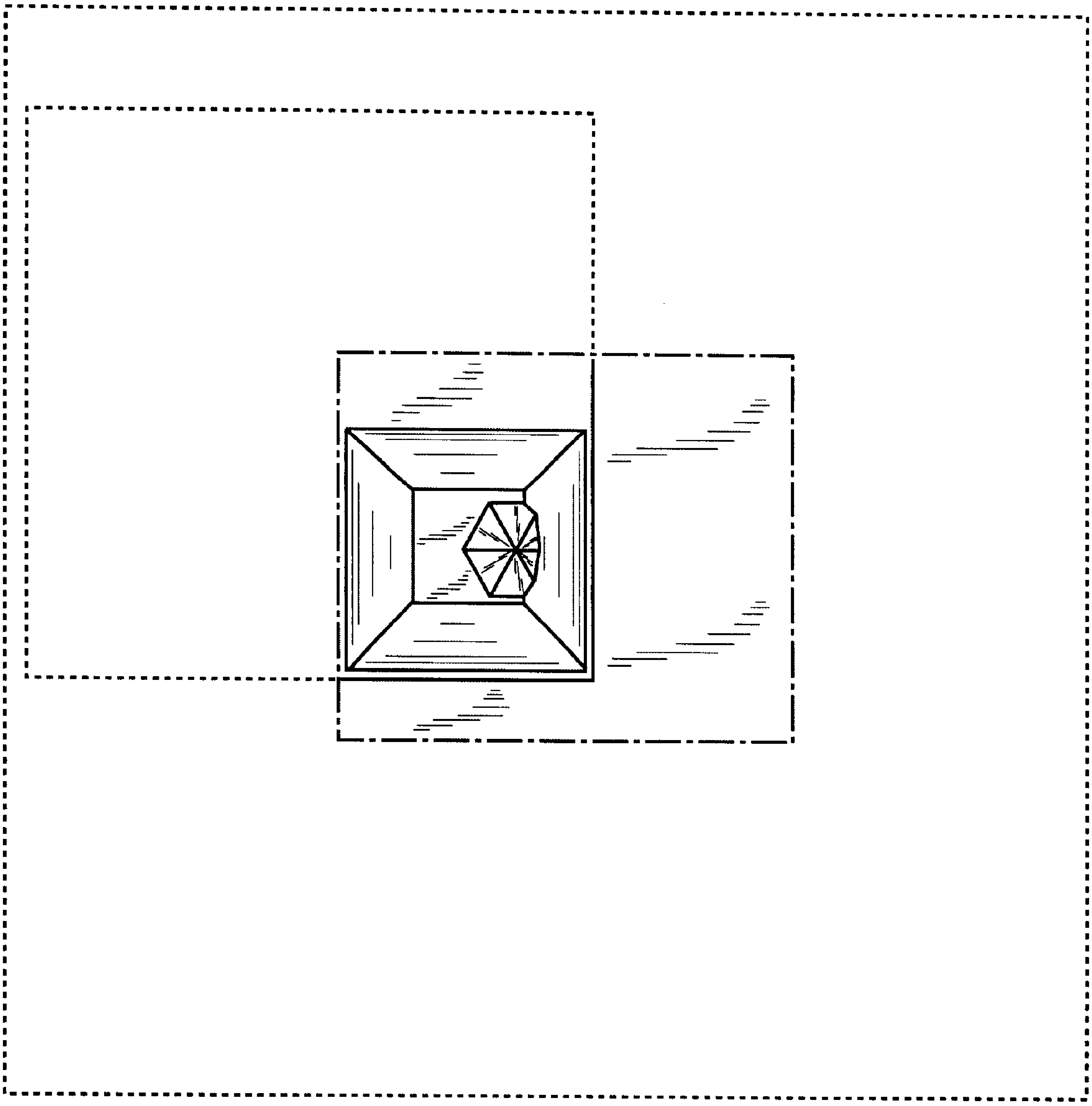


Fig. 7

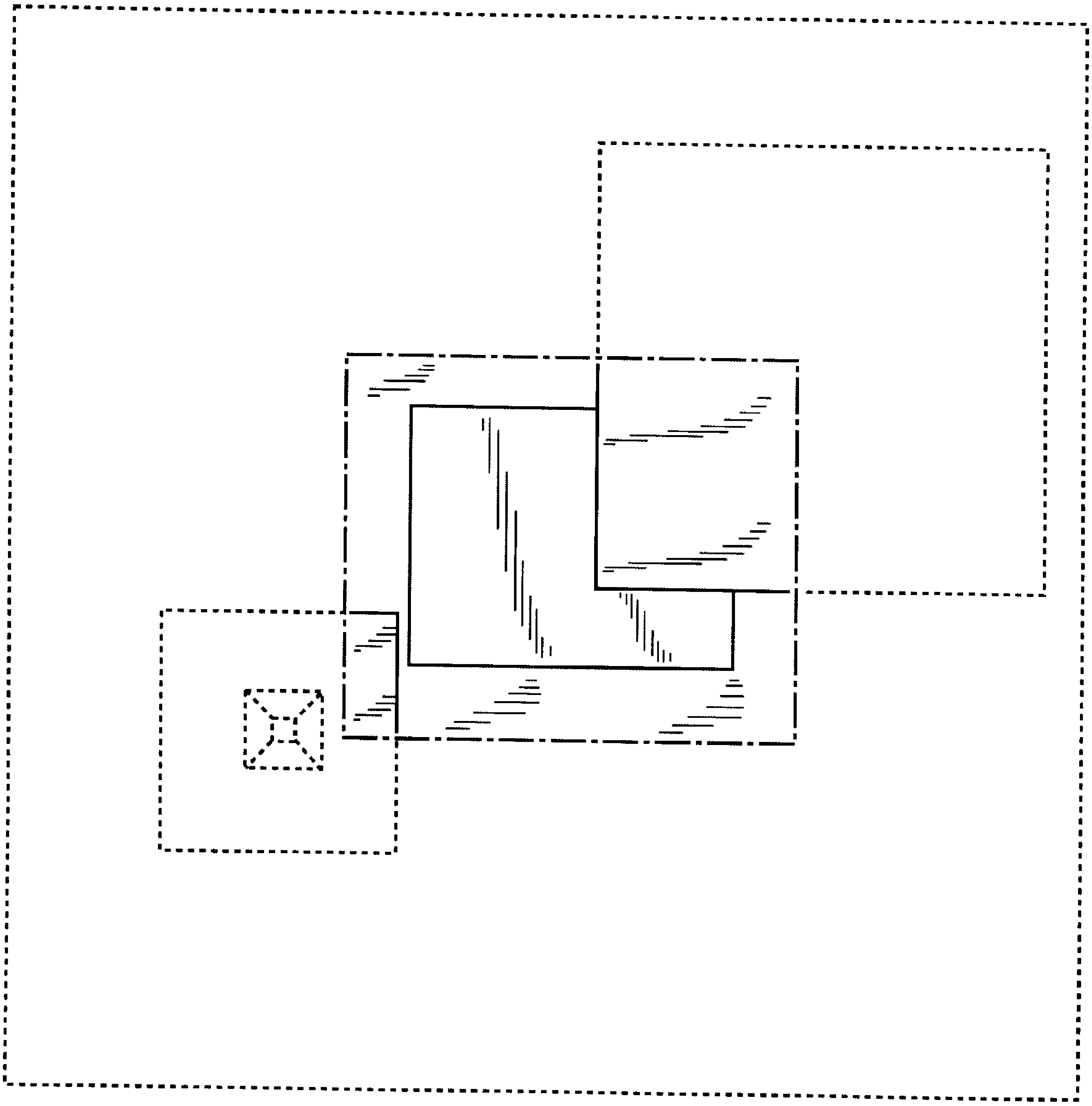


Fig. 8